

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (previously presented) A mask for a nanoprint lithographic process, comprising:  
a translucent material that transfers a pattern from the mask to a substrate when placed in physical contact with the substrate or when placed against the substrate with a predetermined low pressure applied there between;  
one or more three-dimensional features comprising one or more vertical sidewalls;  
an absorbing material deposited upon one or more of the vertical sidewalls so that light incident on an upper surface of the translucent material will be absorbed by the absorbing material, resulting in light blocking features such that upon the transfer of the pattern, the substrate comprises features which directly correspond to areas of the absorbing material deposited on the vertical sidewalls; and  
one or more horizontal surfaces, formed upon one or more of the three-dimensional features, that allow light rays to exit a lower surface of the substrate unobstructed by the absorbing material.
2. (previously presented) The mask of claim 1, the translucent material comprising silicon dioxide.
3. (previously presented) The mask of claim 1, the translucent material being quartz.
4. (original) The mask of claim 1, the absorbing material comprising SiON.
5. (original) The mask of claim 1, the absorbing material comprising Si – rich nitride.
6. (original) The mask of claim 1, the absorbing material comprising Si – rich oxide.

7. (original) The mask of claim 1, the absorbing material comprising SiOCN.
8. (original) The mask of claim 1, the absorbing material comprising TiN.
9. – 23. (cancelled)
24. (new) The mask of claim 1, the absorbing material is a thin film applied by chemical vapor deposition or physical vapor deposition
25. (new) The mask of claim 1 wherein a 1:1 pattern transfer ratio is employed between the mask and the substrate and the dimensions of the resulting area of the substrate are a direct function of the dimensions of the absorbing material on the mask.
26. (new) The mask of claim 1 wherein the absorbing material of the one or more sidewalls has a smaller cross sectional area than the cross sectional area of the one or more horizontal surfaces.
27. (new) A mask for a nanoprnt lithographic process, comprising:
  - a translucent material that transfers a pattern from the mask to a substrate when placed in close proximity to the substrate, when placed in physical contact with the substrate or when placed against the substrate with a predetermined low pressure applied there between;
  - one or more three-dimensional features comprising one or more vertical sidewalls;
  - an absorbing material deposited upon one or more of the vertical sidewalls so that light incident on an upper surface of the translucent material will be absorbed by the absorbing material, resulting in light blocking features such that upon the transfer of the pattern, the substrate comprises features which directly correspond to areas of the absorbing material deposited on the vertical sidewalls; and
  - one or more horizontal surfaces, formed upon one or more of the three-dimensional features, that allow light rays to exit a lower surface of the substrate unobstructed by the absorbing material.

- 28. (new) The mask of claim 27, the translucent material comprising silicon dioxide.
- 29. (new) The mask of claim 27, the translucent material being quartz.
- 30. (new) The mask of claim 27, the absorbing material comprising SiON.
- 31. (new) The mask of claim 27, the absorbing material comprising Si – rich nitride.
- 32. (new) The mask of claim 27, the absorbing material comprising Si – rich oxide.
- 33. (new) The mask of claim 27, the absorbing material comprising SiOCN.
- 34. (new) The mask of claim 27, the absorbing material comprising TiN.
- 35. (new) The mask of claim 27 wherein a 1:1 pattern transfer ratio is employed between the mask and the substrate and the dimensions of the resulting area of the substrate are a direct function of the dimensions of the absorbing material on the mask.